

ABSTRACT OF THE DISCLOSURE

A method for manufacturing a metal-oxide-semiconductor transistor prevents the occurrence of a contact spiking phenomenon. The method includes forming a metal thin film and an isolation oxidation film on a semiconductor substrate, and 5 selectively etching the isolation oxidation film such that the isolation oxidation film is left remaining only over a field oxidation film; heat treating the semiconductor substrate to form silicide by the metal thin film in gate, source, and drain regions; removing portions of the metal thin film that is not formed into silicide, that is, removing unreacted metal thin film; removing the isolation oxidation film left 10 remaining on the field oxidation film; and heat treating the semiconductor substrate in an oxygen environment to form the unreacted metal thin film remaining on the field oxidation film into a metal oxidation film. The present invention is related also to a semiconductor device that employs a metal-oxide-semiconductor transistor made using the method.